

Dual enhanced ultrafast power diode

Rev. 02 - 7 November 2018

Product data sheet

## 1. General description

Dual enhanced ultrafast power diode in a TO220F plastic package.

## 2. Features and benefits

- High thermal cycling performance
- Isolated package
- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state losses

## 3. Applications

- Dual mode (DCM and CCM) PFC
- Power Factor Correction (PFC) for Interleaved Topology

## 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC		-	-	600	V
I <sub>FSM</sub> non-repetitive peak forward current		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode		-	-	132	A
		$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode		-	-	120	A
Static characteristics							
V <sub>F</sub> forward voltage		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>		-	1.4	2.1	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C		-	1.3	1.9	V
Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/µs; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	20	35	ns

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## 5. Pinning information

Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	A1	anode 1	mb					
2	К	cathode						
3	A2	anode 2		K sym125				
mb	n.c.	mounting base; isolated	↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓					

# 6. Ordering information

### Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV410X-600	TO220F	BYV410X-600, 127	Tube	50	SOT186A	14-Nov-2013
BYV410X-600/L01	TO220F	BYV410X-600/L01Q	Tube	50	SOT186A/L01	14-Nov-2013

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## 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>h</sub> ≤ 42 °C; SQW; both diodes conducting; Fig. 1; Fig. 2	-	20	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 $\ ; t_p$ = 25 µs; T_h $\leq \ 60 \ ^\circ C;$ SQW; per diode	-	20	A
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	132	А
	forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	120	А
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C



Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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## 8. Thermal characteristics

Table 5. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	with heatsink compound; per diode; Fig. 3		-	-	5	K/W
		with heatsink compound; both diodes conducting		-	-	3.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air			-	55	-	K/W



Fig. 3. Transient thermal impedance from junction to heatsink per diode as a function of pulse width

# 9. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

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## **10. Characteristics**

Table 7. Characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>		-	1.4	2.1	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C		-	1.3	1.9	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 100 °C		-	1	1.5	mA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C		-	13	50	μA
Dynamic chara	octeristics						
t <sub>rr</sub>	reverse recovery time	$    I_F = 1 \text{ A};  V_R = 30 \text{ V};  dI_F/dt = 100 \text{ A}/\mu\text{s}; \\    T_j = 25 \text{ °C};  \underline{Fig. 5} $		-	20	35	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; <u>Fig. 5</u>		-	1.4	1.9	A
Qr	recovered charge	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/µs		-	15	28	nC
V <sub>FR</sub>	forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 100 A/μs; <u>Fig. 6</u>		-	3.2	-	V



## **WeEn Semiconductors**

# BYV410X-600

## Dual enhanced ultrafast power diode



#### Dual enhanced ultrafast power diode

## 11. Package outline



### Fig. 7. Package outline TO-220F (SOT186A)

BYV410X-600

# **12. Revision history**

Table 8. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYV410X-600 v.2	20181107	Product data sheet	-	BYV410X-600 v.1			
Modifications:	ications: Change from NXP version to WeEn version and update Rth.						
BYV410X-600 v.1	20180920	Product data sheet	-	-			

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## 13. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BYV410X-600

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